

# SN74BCT2410

## 11-BIT MOS MEMORY DRIVER WITH 3-STATE OUTPUTS

SCBS119B – JUNE 1990 – REVISED NOVEMBER 1993

- State-of-the-Art BiCMOS Design Significantly Reduces  $I_{CCZ}$
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model ( $C = 200$  pF,  $R = 0$ )
- Output Ports Have Equivalent  $33\text{-}\Omega$  Series Resistors, So No External Resistors Are Required
- Packaged in Plastic Small-Outline (DW) Package

### description

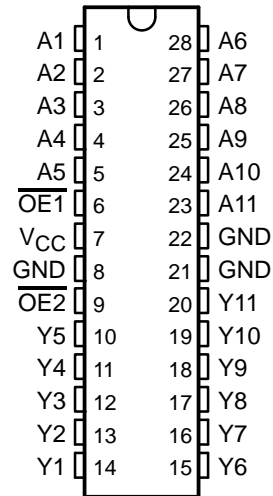
The SN74BCT2410 is a noninverting 11-bit buffer/line driver specifically designed to drive MOS DRAMs of up to 4 megabits. It is also suitable for use with wide data paths or buses carrying parity. The outputs, which are designed to source 1 mA and sink 12 mA, include  $33\text{-}\Omega$  series resistors to reduce overshoot and undershoot.

The output-enable ( $\overline{OE1}$  and  $\overline{OE2}$ ) inputs are routed internally to a two-input AND gate with active-low inputs. When both  $\overline{OE1}$  and  $\overline{OE2}$  are low, the Y outputs are active (high or low logic level). When either  $\overline{OE1}$  or  $\overline{OE2}$  is high, the Y outputs are in the high-impedance state.

The multiple ground pins of the SN74BCT2410 reduce switching noise for more reliable system operation.

The SN74BCT2410 is characterized for operation from  $0^{\circ}\text{C}$  to  $70^{\circ}\text{C}$ .

DW PACKAGE  
(TOP VIEW)



FUNCTION TABLE

INPUTS			OUTPUT Y
$\overline{OE1}$	$\overline{OE2}$	A	
L	L	L	L
L	L	H	H
X	H	X	Z
H	X	X	Z

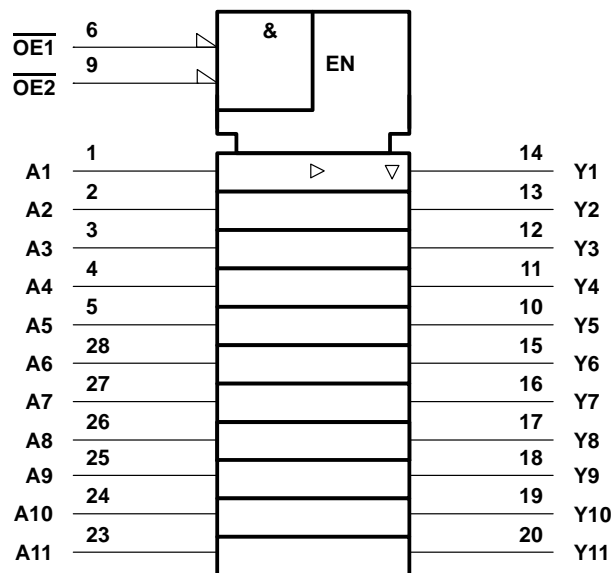
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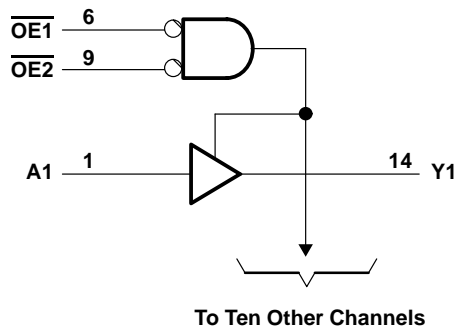
### WITH 3-STATE OUTPUTS

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#### logic symbol†

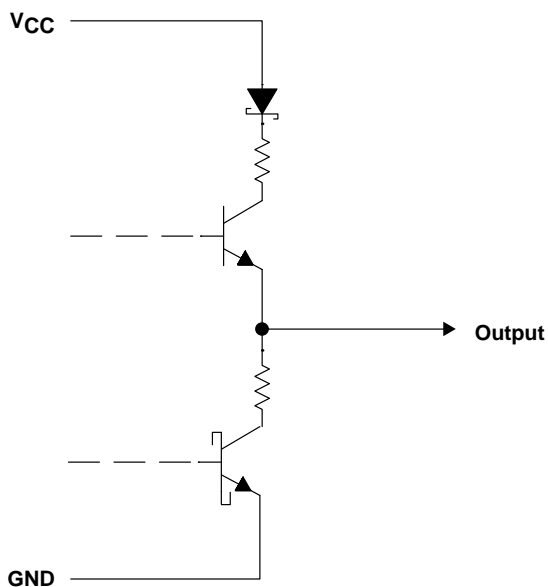


#### logic diagram (positive logic)



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

#### schematic of each output



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**absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†**

Supply voltage range, $V_{CC}$	–0.5 V to 7 V
Input voltage range, $V_I$ (see Note 1)	–0.5 V to 7 V
Voltage range applied to any output in the disabled or power-off state, $V_O$	–0.5 V to 5.5 V
Voltage range applied to any output in the high state, $V_O$	–0.5 V to $V_{CC}$
Input clamp current, $I_{IK}$ ( $V_I < 0$ )	–30 mA
Current into any output in the low state, $I_O$	60 mA
Operating free-air temperature range	0°C to 70°C
Storage temperature range	–65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: The input negative-voltage rating may be exceeded if the input clamp-current rating is observed.

**recommended operating conditions (see Note 2)**

	MIN	NOM	MAX	UNIT
$V_{CC}$ Supply voltage	4.5	5	5.5	V
$V_{IH}$ High-level input voltage	2			V
$V_{IL}$ Low-level input voltage			0.8	V
$I_{IK}$ Input clamp current			–18	mA
$I_{OH}$ High-level output current			–12	mA
$I_{OL}$ Low-level output current			12	mA
$T_A$ Operating free-air temperature	0		70	°C

NOTE 2: Unused or floating inputs must be held high or low.

**electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)**

PARAMETER	TEST CONDITIONS		MIN	TYP‡	MAX	UNIT
$V_{IK}$	$V_{CC} = 4.5$ V,	$I_I = -18$ mA			–1.2	V
$V_{OH}$	$V_{CC} = 4.5$ V	$I_{OH} = -3$ mA	2.5	3.5		V
		$I_{OH} = -12$ mA	2	3.1		
$V_{OL}$	$V_{CC} = 4.5$ V,	$I_{OL} = 12$ mA		0.42	0.8	V
$I_I$	$V_{CC} = 5.5$ V,	$V_I = 5.5$ V			0.1	mA
$I_{IH}$	$V_{CC} = 5.5$ V,	$V_I = 2.7$ V			20	µA
$I_{IL}$	$V_{CC} = 5.5$ V,	$V_I = 0.5$ V			–0.1	mA
$I_{OZH}$	$V_{CC} = 5.5$ V,	$V_O = 2.7$ V			50	µA
$I_{OZL}$	$V_{CC} = 5.5$ V,	$V_O = 0.5$ V			–50	µA
$I_O^§$	$V_{CC} = 5.5$ V,	$V_O = 2.25$ V	–15		–70	mA
$I_{CCL}$	$V_{CC} = 5.5$ V,	$V_O = 0$			40	mA
$I_{CCH}$	$V_{CC} = 5.5$ V,	$V_O = 0$			40	mA
$I_{CCZ}$	$V_{CC} = 5.5$ V,	$V_O = 0$			6.5	mA
$C_i$	$V_{CC} = 5$ V,	$V_I = 2.5$ V or 0.5 V		6		pF
$C_O$	$V_{CC} = 5$ V,	$V_O = 2.5$ V or 0.5 V		10		pF

‡ All typical values are at  $V_{CC} = 5$  V,  $T_A = 25^\circ\text{C}$ .

§ Not more than one output should be tested at a time, and the duration of the test should not exceed one second.



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switching characteristics over recommended ranges of supply voltage and operating free-air temperature,  $C_L = 50$  pF (unless otherwise noted) (see Note 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 5$ V, $T_A = 25^\circ\text{C}$			MIN	MAX	UNIT
			MIN	TYP	MAX			
$t_{PLH}$	A	Y	2	4.9	6.5	2	8.5	ns
$t_{PHL}$			2.3	5.6	7.5	2.3	8.5	
$t_{PZH}$	$\overline{OE}$	Y	4.5	10.3	13	4.5	16.5	ns
$t_{PZL}$			2	11.4	16	2	19	
$t_{PHZ}$	$\overline{OE}$	Y	3.4	7	9.5	3.4	12	ns
$t_{PLZ}$			5.3	9.2	11.5	5.3	13.5	

NOTE 3: Load circuits and voltage waveforms are shown in Section 1.

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